# Low-Voltage CMOS Octal Buffer

## With 5 V-Tolerant Inputs and Outputs (3-State, Non-Inverting)

The MC74LCX244 is a high performance, non–inverting octal buffer operating from a 2.3 to 5.5 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V<sub>I</sub> specification of 5.5 V allows MC74LCX244 inputs to be safely driven from 5 V devices. The MC74LCX244 is suitable for memory address driving and all TTL level bus oriented transceiver applications.

Current drive capability is 24 mA at the outputs. The Output Enable  $(\overline{OE})$  input, when HIGH, disables the output by placing them in a HIGH Z condition.

#### **Features**

- Designed for 2.3 to 5.5 V V<sub>CC</sub> Operation
- 5 V Tolerant Interface Capability With 5 V TTL Logic
- Supports Live Insertion and Withdrawal
- I<sub>OFF</sub> Specification Guarantees High Impedance When V<sub>CC</sub> = 0 V
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10 μA)
   Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance:
  - ♦ Human Body Model >2000 V
  - ♦ Machine Model >200 V
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



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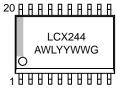


SOIC-20 WB DW SUFFIX CASE 751D

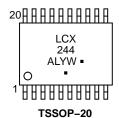
TSSOP-20 DT SUFFIX CASE 948E

QFN20 MN SUFFIX CASES 485AA & 485CB

#### **MARKING DIAGRAMS**



SOIC-20 WB



1 0 LCX 244 ALYW•



QFN20 - 485AA

QFN20 - 485CB

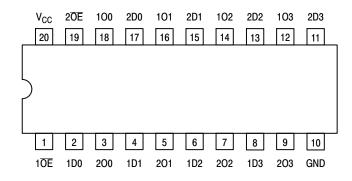
A = Assembly Location
L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week

G or ■ = Pb–Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.



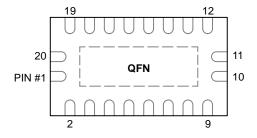


Figure 1. Pinouts: 20-Lead (Top View)

#### **PIN NAMES**

PINS	FUNCTION	
nOE	Output Enable Inputs	
1Dn, 2Dn	Data Inputs	
1On, 2On	3-State Outputs	

#### **TRUTH TABLE**

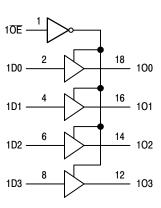
INPUTS		OUTPUTS
1 <u>0E</u> 2 <u>0E</u>	1Dn 2Dn	10n, 20n
L	L	L
L	Н	Н
Н	Х	Z

H = High Voltage Level

L = Low Voltage Level

Z = High Impedance State
X = High or Low Voltage Level and Transitions are Acceptable

For I<sub>CC</sub> reasons, DO NOT FLOAT Inputs



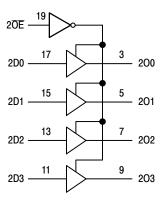


Figure 2. Logic Diagram

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Condition	Units
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_{O} \le +7.0$	Output in 3-State	V
		$-0.5 \le V_O \le V_{CC} + 0.5$	Output in HIGH or LOW State (Note 1)	V
I <sub>IK</sub>	DC Input Diode Current	-50	V <sub>I</sub> < GND	mA
I <sub>OK</sub>	DC Output Diode Current	-50	V <sub>O</sub> < GND	mA
		+50	Vo > Vcc	mA
I <sub>O</sub>	DC Output Source/Sink Current	±50		mA
Icc	DC Supply Current Per Supply Pin	±100		mA
I <sub>GND</sub>	DC Ground Current Per Ground Pin	±100		mA
T <sub>STG</sub>	Storage Temperature Range	-65 to +150		°C
T <sub>L</sub>	Lead Temperature, 1 mm from Case for 10 Seconds	T <sub>L</sub> = 260		°C
TJ	Junction Temperature Under Bias	$T_{J} = 150$		°C
$\theta_{JA}$	Thermal Resistance (Note 2)	θ <sub>JA</sub> = 140		°C/W
MSL	Moisture Sensitivity		Level 1	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Тур	Max	Units
V <sub>CC</sub>	Supply Voltage Operating Data Retention Only	2.0 1.5	2.5, 3.3 2.5, 3.3	5.5 5.5	V
VI	Input Voltage	0		5.5	V
Vo	Output Voltage HIGH or LOW State 3-State	0		V <sub>CC</sub> 5.5	V
I <sub>OH</sub>	HIGH Level Output Current $V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$ $V_{CC} = 2.7 \text{ V} - 3.0 \text{ V}$			-24 -12	mA
loL	LOW Level Output Current $V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$ $V_{CC} = 2.7 \text{ V} - 3.0 \text{ V}$			24 12	mA
T <sub>A</sub>	Operating Free–Air Temperature	-55		+125	°C
Δt/ΔV	Input Transition Rise or Fall Rate, $V_{IN}$ from 0.8 V to 2.0 V, $V_{CC}$ = 3.0 V	0		10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

I<sub>O</sub> absolute maximum rating must be observed.
 Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow.

#### DC ELECTRICAL CHARACTERISTICS

			T <sub>A</sub> = −55°C	to +125°C	
Symbol	Characteristic	Condition	Min	Max	Units
V <sub>IH</sub>	HIGH Level Input Voltage (Note 3)	2.3 V ≤ V <sub>CC</sub> ≤ 2.7 V	1.7		V
		2.7 V ≤ V <sub>CC</sub> ≤ 3.6 V	2.0		]
V <sub>IL</sub>	LOW Level Input Voltage (Note 3)	2.3 V ≤ V <sub>CC</sub> ≤ 2.7 V		0.7	V
		2.7 V ≤ V <sub>CC</sub> ≤ 3.6 V		0.8	
V <sub>OH</sub>	HIGH Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$	V <sub>CC</sub> - 0.2		V
		$V_{CC} = 2.3 \text{ V; } I_{OH} = -8 \text{ mA}$	1.8		]
		$V_{CC} = 2.7 \text{ V; } I_{OH} = -12 \text{ mA}$	2.2		]
		$V_{CC} = 3.0 \text{ V; } I_{OH} = -18 \text{ mA}$	2.4		
		$V_{CC} = 3.0 \text{ V; } I_{OH} = -24 \text{ mA}$	2.2		
V <sub>OL</sub>	LOW Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$		0.2	V
		$V_{CC} = 2.3 \text{ V; } I_{OL} = 8 \text{ mA}$		0.6	
		$V_{CC} = 2.7 \text{ V}; I_{OL} = 12 \text{ mA}$		0.4	
		$V_{CC} = 3.0 \text{ V}; I_{OL} = 16 \text{ mA}$		0.4	
		$V_{CC} = 3.0 \text{ V}; I_{OL} = 24 \text{ mA}$		0.55	
l <sub>OZ</sub>	3-State Output Current	$V_{CC} = 3.6 \text{ V}, V_{IN} = V_{IH} \text{ or } V_{IL}, V_{OUT} = 0 \text{ to } 5.5 \text{ V}$		±5	μΑ
I <sub>OFF</sub>	Power Off Leakage Current	$V_{CC} = 0$ , $V_{IN} = 5.5$ V or $V_{OUT} = 5.5$ V		10	μΑ
I <sub>IN</sub>	Input Leakage Current	V <sub>CC</sub> = 3.6 V, V <sub>IN</sub> = 5.5 V or GND		±5	μΑ
I <sub>CC</sub>	Quiescent Supply Current	V <sub>CC</sub> = 3.6 V, V <sub>IN</sub> = 5.5 V or GND		10	μΑ
$\Delta I_{CC}$	Increase in I <sub>CC</sub> per Input	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_{IH} = V_{CC} - 0.6 \text{ V}$		500	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. These values of  $V_I$  are used to test DC electrical characteristics only.

#### AC CHARACTERISTICS ( $t_R = t_F = 2.5 \text{ ns}; R_L = 500 \Omega$ )

					Lin	nits			
					$T_A = -55^{\circ}C$	to +125°C			
			V <sub>CC</sub> = 3.0	V to 3.6 V	V <sub>CC</sub> =	: 2.7 V	V <sub>CC</sub> = 2.	5 V ± 0.2	
			C <sub>L</sub> =	50 pF	C <sub>L</sub> =	50 pF	C <sub>L</sub> =	30 pF	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Min	Max	Units
t <sub>PLH</sub>	Propagation Delay Input to Output	1	1.5 1.5	6.5 6.5	1.5 1.5	7.5 7.5	1.5 1.5	7.8 7.8	ns
t <sub>PZH</sub>	Output Enable Time to High and Low Level	2	1.5 1.5	8.0 8.0	1.5 1.5	9.0 9.0	1.5 1.5	10 10	ns
t <sub>PHZ</sub>	Output Disable Time From High and Low Level	2	1.5 1.5	7.0 7.0	1.5 1.5	8.0 8.0	1.5 1.5	8.4 8.4	ns
t <sub>OSHL</sub> t <sub>OSLH</sub>	Output-to-Output Skew (Note 4)			1.0 1.0					ns

<sup>4.</sup> Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH–to–LOW (t<sub>OSHL</sub>) or LOW–to–HIGH (t<sub>OSLH</sub>); parameter guaranteed by design.

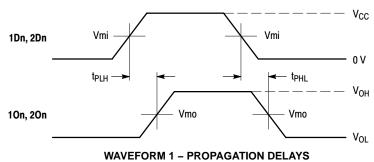
#### **DYNAMIC SWITCHING CHARACTERISTICS**

			Т	A = +25°C	;	
Symbol	Characteristic	Condition	Min	Тур	Max	Units
V <sub>OLP</sub>	Dynamic LOW Peak Voltage (Note 5)	$\begin{array}{c} V_{CC} = 3.3 \text{ V, } C_L = 50 \text{ pF, } V_{IH} = 3.3 \text{ V, } V_{IL} = 0 \text{ V} \\ V_{CC} = 2.5 \text{ V, } C_L = 30 \text{ pF, } V_{IH} = 2.5 \text{ V, } V_{IL} = 0 \text{ V} \end{array}$		0.8 0.6		V
V <sub>OLV</sub>	Dynamic LOW Valley Voltage (Note 5)	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ $V_{CC} = 2.5 \text{ V}, C_L = 30 \text{ pF}, V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$		-0.8 -0.6		V

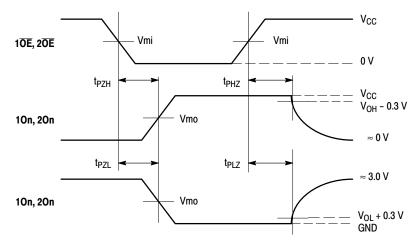
<sup>5.</sup> Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

#### **CAPACITIVE CHARACTERISTICS**

Symbol	Parameter	Condition	Typical	Units
C <sub>IN</sub>	Input Capacitance	$V_{CC} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	7	pF
C <sub>OUT</sub>	Output Capacitance	$V_{CC}$ = 3.3 V, $V_{I}$ = 0 V or $V_{CC}$	8	pF
C <sub>PD</sub>	Power Dissipation Capacitance	10 MHz, $V_{CC}$ = 3.3 V, $V_{I}$ = 0 V or $V_{CC}$	25	pF



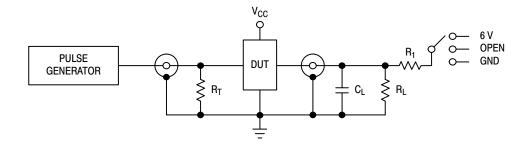
 $t_R = t_F = 2.5 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$ 



### WAVEFORM 2 – OUTPUT ENABLE AND DISABLE TIMES $t_R=t_F=2.5~\text{ns},~10\%~\text{to}~90\%;~f=1~\text{MHz};~t_W=500~\text{ns}$

Figure 3. AC Waveforms

	V <sub>CC</sub>				
Symbol	3.3 V $\pm$ 0.3 V	2.7 V	2.5 V $\pm$ 0.2 V		
Vmi	1.5 V	1.5 V	V <sub>CC</sub> /2		
Vmo	1.5 V	1.5 V	V <sub>CC</sub> /2		
$V_{HZ}$	V <sub>OL</sub> + 0.3 V	V <sub>OL</sub> + 0.3 V	V <sub>OL</sub> + 0.15 V		
$V_{LZ}$	V <sub>OH</sub> – 0.3 V	V <sub>OH</sub> – 0.3 V	V <sub>OH</sub> – 015 V		



TEST	SWITCH
t <sub>PLH</sub> , t <sub>PHL</sub>	Open
t <sub>PZL</sub> , t <sub>PLZ</sub>	6 V at $V_{CC} = 3.3 \pm 0.3 \text{ V}$ 6 V at $V_{CC} = 2.5 \pm 0.2 \text{ V}$
Open Collector/Drain t <sub>PLH</sub> and t <sub>PHL</sub>	6 V
t <sub>PZH</sub> , t <sub>PHZ</sub>	GND

 $C_L$  = 50 pF at  $V_{CC}$  = 3.3 ± 0.3 V or equivalent (includes jig and probe capacitance)  $C_L$  = 30 pF at  $V_{CC}$  = 2.5 ± 0.2 V or equivalent (includes jig and probe capacitance)  $R_L$  =  $R_1$  = 500  $\Omega$  or equivalent  $R_T$  =  $Z_{OUT}$  of pulse generator (typically 50  $\Omega$ )

Figure 4. Test Circuit

#### **ORDERING INFORMATION**

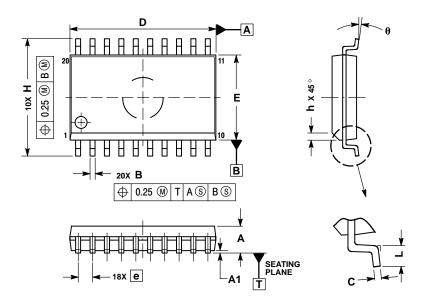
Device	Package	Shipping <sup>†</sup>
MC74LCX244DWG	SOIC-20 WB (Pb-Free)	38 Units / Rail
MC74LCX244DWR2G	SOIC-20 WB (Pb-Free)	1000 / Tape & Reel
MC74LCX244DTG	TSSOP-20 (Pb-Free)	75 Units / Rail
MC74LCX244DTR2G	TSSOP-20 (Pb-Free)	2500 / Tape & Reel
NLV74LCX244DTR2G*	TSSOP-20 (Pb-Free)	2500 / Tape & Reel
MC74LCX244MNTWG	QFN20, 2.5x4.5 (Pb-Free)	3000 / Tape & Reel
MC74LCX244MN2TWG	QFN20, 2.5x3.5 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable

#### PACKAGE DIMENSIONS

#### SOIC-20 WB CASE 751D-05 **ISSUE H**



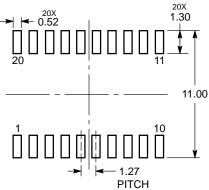
#### NOTES:

- NOTES:

  1. DIMENSIONS ARE IN MILLIMETERS.
  2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
  4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
  5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.35	2.65	
A1	0.10	0.25	
В	0.35	0.49	
C	0.23	0.32	
D	12.65	12.95	
Е	7.40	7.60	
е	1.27	BSC	
Н	10.05	10.55	
h	0.25	0.75	
L	0.50	0.90	
θ	0 °	7 °	

#### **RECOMMENDED SOLDERING FOOTPRINT\***

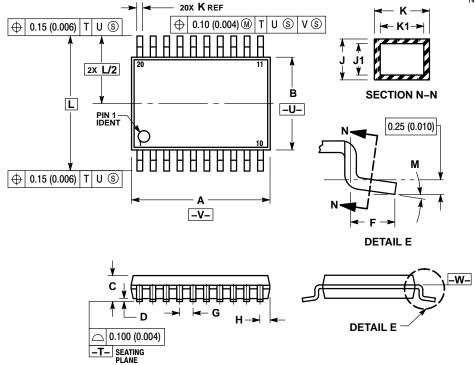


DIMENSIONS: MILLIMETERS

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

#### TSSOP-20 CASE 948E ISSUE D



#### NOTES:

- DIES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION:
  MILLIMETER.

- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE
- MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

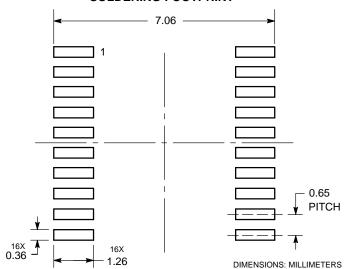
  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
- (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

  6. TERMINAL NUMBERS ARE SHOWN FOR
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE —W—.

<u> </u>		IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

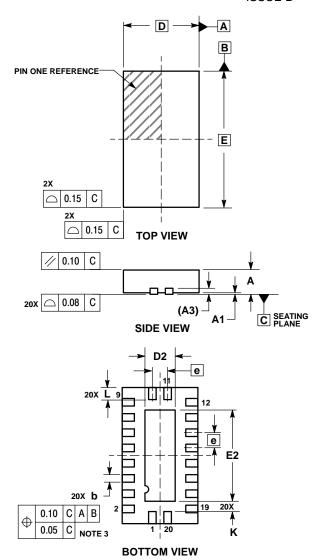
#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **PACKAGE DIMENSIONS**

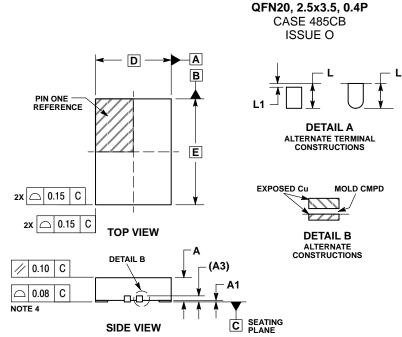
#### QFN20, 2.5x4.5 MM CASE 485AA ISSUE B



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. DIMENSIONS b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
  4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.80	1.00		
A1	0.00	0.05		
A3	0.20	0.20 REF		
b	0.20	0.30		
D	2.50 BSC			
D2	0.85	1.15		
E	4.50 BSC			
E2	2.85	3.15		
е	0.50 BSC			
K	0.20			
	0.35	0.45		

#### PACKAGE DIMENSIONS



0.10 C A B

E2

 $\Phi$ 

0.10 C A B

20X b

0.10 C A B

0.05 C NOTE 3

Ф

D2

**BOTTOM VIEW** 

DETAIL A

е

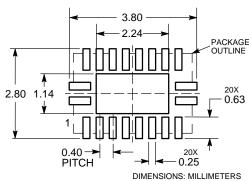
e/2

#### NOTES

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSIONS b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM TERMINAL TIP.
  COPLANARITY APPLIES TO THE EXPOSED
- PAD AS WELL AS THE TERMINALS.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.80	1.00	
A1	0.00	0.05	
A3	0.20 REF		
b	0.15	0.25	
D	2.50 BSC		
D2	0.90	1.10	
Е	3.50 BSC		
E2	2.00	2.20	
е	0.40 BSC		
L	0.35	0.45	
11		0.15	

#### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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